

**AMENDMENTS TO THE SPECIFICATION**

On page 1, before “Field of the Invention,” please insert -- This application is a continuation of Application Serial No. 10/118,947, filed April 10, 2002, which in turn is a divisional of Application Serial No. 09/650,071, filed on August 29, 2000, the subject matter of both of which is incorporated by reference herein. --

Please replace the current title with the following new title:

**METAL TO POLYSILICON CONTACT IN OXYGEN ENVIRONMENT**

On page 14 (lines 24-25) continuing on page 15 (lines 1-11):

(Amended) Figure 18 shows a second embodiment of the invention, which uses a first and second oxygen sink spacers, 61 and 71, respectively, as well as a first and second metal layers, 62 and 72, respectively, formed before a ~~first~~ second oxygen sink layer 64 is formed. Layers 62, 71, 72 and 64 are sequentially formed in a way similar to that employed for the formation of metal layer 62 (Figure 13) and oxygen sink layer 64 (Figures 14-15), described with respect to the formation of the first embodiment of the present invention. As shown in Figure 18, each of the layers 62, 71, 72 and 64 is chemical mechanical polished (CMP) so that each of their upper surfaces end at the upper surface of the second insulating layer 25, where a capacitor structure can be built in the manner shown and described with reference to Figures 16 and 17. Of course, as explained above, layers 62, 71, 72 and 64 could extend over and cover the upper surfaces of the second insulating layer 25, as long as the conductor 81 of a fabricated overlying capacitor can connect with conductive layers 62 and 72.